TEXAS INSTRUMENTS
LMK1C1102, LMK1C1103, LMK1C1104
JAJSIA5D – DECEMBER 2019 – REVISED FEBRUARY 2022

LMK1C110x 1.8V、2.5V、3.3V LVCMOS クロック・バッファ・ファミリ

1 特長

- 高性能の 1:2、1:3、1:4 LVCMOS クロック・バッファ
- 非常に小さい出力スキュー:50ps 未満
- 非常に小さい付加ジッタ:50fs 未満
  - V_{DD} = 3.3V で 7.5fs (標準値)
  - V_{DD} = 2.5V で 10fs (標準値)
  - V_{DD} = 1.8V で 19.2fs (標準値)
- 超低速伝播遅延:3ns 未満
- 同期出力イネーブル
- 電源電圧:3.3V、2.5V、1.8V
  - 3.3V トレラント入力機能 (すべての電源電圧で対応)
  - フェイルセーフ入力
- 3.3V で f_{max} = 250MHz
  2.5V および 1.8V で f_{max} = 200MHz
- 動作温度範囲:–40℃～125℃
- 8 ピンの TSSOP パッケージで供給
- 8 ピンの WSON パッケージで供給

2 アプリケーション

- ファクトリ・オートメーション / 制御
- 通信機器
- データ・センターおよびエンタープライズ・コンピューティング
- グリッド・インフラストラクチャ
- モーター・ドライブ
- 医療用画像処理

3 概要

LMK1C110x は、テキサス・インスツルメンツ製の高性能、低スキューのモジュール式汎用クロック・バッファ・ファミリです。このファミリはすべて、モジュール手法を考慮して設計されています。1:2、1:3、1:4 の 3 種類のファンアウト・バリエーションがあります。

このファミリに属するデバイスはすべて互いにピン互換であり、CDCLVC110x ファミリと後方互換性があるため扱いが簡単です。

ファミリのすべての製品は、小さい付加ジッタ、小さいスキュー、広い動作温度範囲などの高い性能を共有しています。

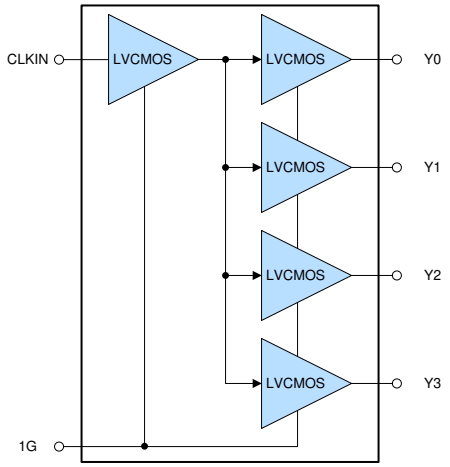
LMK1C110x は、1G が LOW になると出力を LOW 状態に切り換える同期出力イネーブル制御 (1G) をサポートしています。これらのデバイスにはフェイルセーフ入力があり、入力信号がない場合の出力の発振を防止し、VDD が供給される前に入力信号を受け入れます。

LMK1C110x ファミリは 1.8V、2.5V、3.3V 環境で動作し、–40℃～125℃で動作が規定されています。

製品情報(1)

部品番号	パッケージ	本体サイズ (公称)
LMK1C1102	TSSOP (8)	3.00mm × 4.40mm
LMK1C1103		
LMK1C1104		
LMK1C1102	WSON (8)	2.00mm × 2.00mm
LMK1C1104		

(1) 利用可能なパッケージについては、このデータシートの末尾にある注文情報を参照してください。



機能ブロック図

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Changes from Revision C (June 2021) to Revision D (February 2022) — **Page**

- 「概要」セクションにフェイルセーフ入力の詳細を追加 ... 1
- Changed part-to-part skew maximum from 450 ps to 250 ps ... 6
- Added the *Fail-Safe Inputs* section ... 10

Changes from Revision B (June 2020) to Revision C (June 2021) — **Page**

- 文書全体にわたってテキスト形式、表、図、相互参照の採番方法を変更 ... 1
- LMK1C1102/04 DQF (WSON) パッケージを追加 ... 1
- Added the *Device Comparison* table ... 3
- Added pinout diagrams for the DQF (WSON) package variant of the LMK1C1102 and LMK1C1104 ... 3
- Added information pertaining to the layout of LMK1C1102/04 WSON package variant ... 14
- Removed *Related Links* section ... 15

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- 「*概要*」セクションにファンアウト・バリエーションの情報を追加 ... 1
- 先頭ページから LMK1C1104PW のピン配置を削除 ... 1
- Added LMK1C1102 and LMK1C1103 pinout diagrams ... 3

Changes from Revision * (December 2019) to Revision A (February 2020) — **Page**

- データシートに LMK1C1102 と LMK1C1103 を追加 ... 1
- Changed the *Power Supply Recommendations* section ... 13

5 Device Comparison

表 5-1. Device Comparison

DEVICE	NUMBER OF OUTPUTS	PACKAGE
LMK1C1102	2	TSSOP (8), 3.00 mm x 4.40 mm
LMK1C1103	3	
LMK1C1104	4	
LMK1C1106	6	TSSOP (14), 5.00 mm x 4.40 mm
LMK1C1108	8	TSSOP (16), 5.00 mm x 4.40 mm
LMK1C1102	2	WSON (8), 2.00 mm x 2.00 mm
LMK1C1104	4	

6 Pin Configuration and Functions

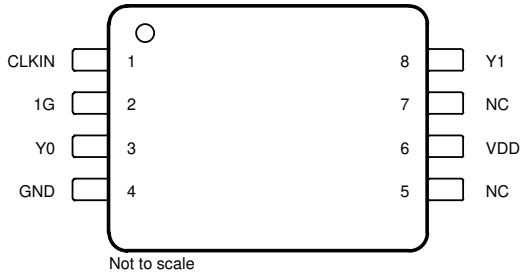
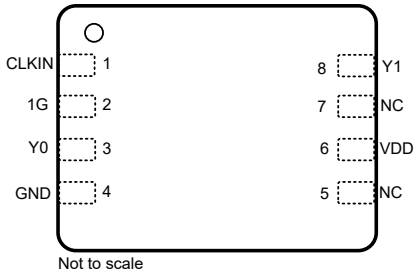


図 6-1. LMK1C1102 PW Package 8-Pin TSSOP Top View



1. The DQF (WSON) package is equivalent to the DFN package of other vendors.

図 6-2. LMK1C1102 DQF Package 8-Pin WSON Top View

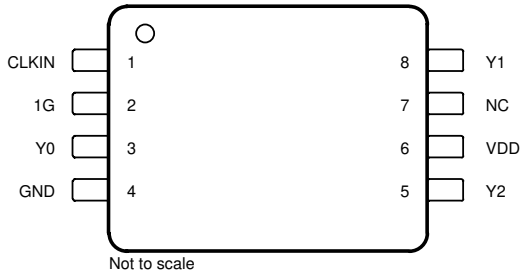


図 6-3. LMK1C1103 PW Package 8-Pin TSSOP Top View

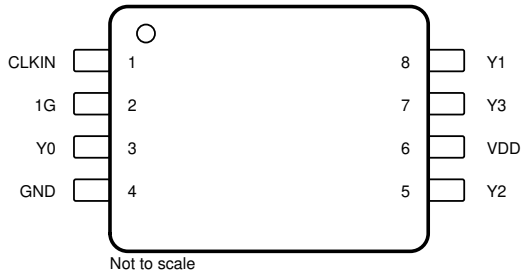
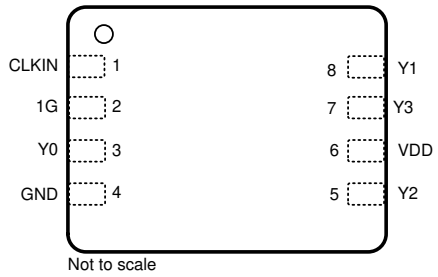


図 6-4. LMK1C1104 PW Package 8-Pin TSSOP Top View



1. The DQF (WSON) package is equivalent to the DFN package of other vendors.

図 6-5. LMK1C1104 DQF Package 8-Pin WSON Top View

表 6-1. Pin Functions

PIN				TYPE	DESCRIPTION
NAME	LMK1C1102	LMK1C1103	LMK1C1104		
LVCMOS CLOCK INPUT					
CLKIN	1	1	1	Input	Single-ended clock input with internal 300-kΩ (typical) pulldown resistor to GND. Typically connected to a single-ended clock input.
CLOCK OUTPUT ENABLE					
1G	2	2	2	Input	Global Output Enable with internal 300-kΩ (typical) pulldown resistor to GND. Typically connected to VDD with external pullup resistor. HIGH: outputs enabled LOW: outputs disabled
LVCMOS CLOCK OUTPUT					
Y0	3	3	3	Output	LVCMOS output. Typically connected to a receiver. Unused outputs can be left floating.
Y1	8	8	8		
Y2	—	5	5		
Y3	—	—	7		
SUPPLY VOLTAGE					
VDD	6	6	6	Power	Power supply terminal. Typically connected to a 3.3-V, 2.5-V, or 1.8-V supply. The VDD pin is typically connected to an external 0.1-µF capacitor near the pin.
GROUND					
GND	4	4	4	GND	Power supply ground.

7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

		MIN	MAX	UNIT
V_{DD}	Supply voltage	–0.5	3.6	V
V_{CLKIN}	Input voltage (CLKIN)			
V_{IN}	Input voltage (1G)			
V_{Yn}	Output pins (Yn)	–0.5	V_{DD} + 0.3	
I_{IN}	Input current	–20	20	mA
I_O	Continuous output current	–50	50	mA
T_{stg}	Storage temperature	–65	150	°C

(1) Operation outside the *Absolute Maximum Ratings* may cause permanent device damage. *Absolute Maximum Ratings* do not imply functional operation of the device at these or any other conditions beyond those listed under *Recommended Operating Conditions*. If used outside the *Recommended Operating Conditions* but within the *Absolute Maximum Ratings*, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.

7.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins(1)	±9000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins(2)	±1500	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	NOM	MAX	UNIT
V_{DD}	Core supply voltage	3.3-V supply	3.135	3.3	3.465	V
		2.5-V supply	2.375	2.5	2.625	
		1.8-V supply	1.71	1.8	1.89	
T_A	Operating free-air temperature		–40		125	°C
T_J	Operating junction temperature		–40		150	°C

7.4 Thermal Information

THERMAL METRIC(1)		LMK1C1104		UNIT
		DQF(WSON)	PW (TSSOP)	
		8 PINS	8 PINS	
R_{qJA}	Junction-to-ambient thermal resistance	163	181.9	°C/W
$R_{qJC(top)}$	Junction-to-case (top) thermal resistance	105.7	76.6	°C/W
R_{qJB}	Junction-to-board thermal resistance	84.2	111.6	°C/W
Y_{JT}	Junction-to-top characterization parameter	16.7	16	°C/W
Y_{JB}	Junction-to-board characterization parameter	83.9	110.1	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

7.5 Electrical Characteristics

VDD = 3.3 V ± 5 %, –40°C ≤ TA ≤ 125°C. Typical values are at VDD = 3.3 V, 25°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
CURRENT CONSUMPTION						
I_{DD}	Core supply current, static	All-outputs disabled, f_{IN} = 0 V		25	45	µA
I_{DD}	Core supply current	All-outputs disabled, f_{IN} = 100 MHz		8	15	mA
		All-outputs active, f_{IN} = 100 MHz, C_L = 5pF, V_{DD} = 1.8 V		14	20	
		All-outputs active, f_{IN} = 100 MHz, C_L = 5pF, V_{DD} = 2.5 V		21	30	
		All-outputs active, f_{IN} = 100 MHz, C_L = 5pF, V_{DD} = 3.3 V		33	40	
CLOCK INPUT						
f_{IN_SE}	Input frequency	V_{DD} = 3.3 V	DC		250	MHz
		V_{DD} = 2.5 V and 1.8 V	DC		200	
V_{IH}	Input high voltage		0.7 x V_{DD}			V
V_{IL}	Input low voltage				0.3 x V_{DD}	
dV_{IN}/dt	Input slew rate	20% - 80% of input swing	0.1			V/ns
I_{IN_LEAK}	Input leakage current		–50		50	uA
C_{IN_SE}	Input capacitance	at 25°C		7		pF
CLOCK OUTPUT FOR ALL V_{DD} LEVELS						
f_{OUT}	Output frequency	V_{DD} = 3.3 V			250	MHz
		V_{DD} = 2.5 V and 1.8 V			200	
ODC	Output duty cycle	With 50% duty cycle input (for all VDD)	45		55	%
t_{START}	Start-up time before output is active	See (1)			3	ms
t_{1G_ON}	Output enable time	See (2)			5	cycles
t_{1G_OFF}	Output disable time	See (3)			5	cycles
CLOCK OUTPUT FOR V_{DD} = 3.3 V ± 5%						
V_{OH}	Output high voltage	I_{OH} = 1 mA	2.8			V
V_{OL}	Output low voltage	I_{OL} = 1 mA			0.2	
$t_{RISE-FALL}$	Output rise and fall time	20/80%, C_L= 5 pF, fIN = 156.25 MHz		0.35	0.7	ns
$t_{OUTPUT-SKEW}$	Output-output skew	See (4)		25	50	ps
$t_{PART-SKEW}$	Part-to-part skew				250	
$t_{PROP-DELAY}$	Propagation delay	See (5)		1.5	2	ns
$t_{JITTER-ADD}$	Additive Jitter	f_{IN} = 156.25 MHz, Input slew rate = 2 V/ns, Integration range = 12 kHz - 20 MHz		8	20	fs, RMS
R_{OUT}	Output impedance			50		Ω
CLOCK OUTPUT FOR V_{DD} = 2.5 V ± 5%						
V_{OH}	Output high voltage	I_{OH} = 1 mA	0.8 x V_{DD}			V
V_{OL}	Output low voltage	I_{OL} = 1 mA			0.2 x V_{DD}	
$t_{RISE-FALL}$	Output rise and fall time	20/80%, C_L= 5 pF, f_{IN} = 156.25 MHz		0.33	0.8	ns
$t_{OUTPUT-SKEW}$	Output-output skew	See (4)			50	ps
$t_{PART-SKEW}$	Part-to-part skew				400	
$t_{PROP-DELAY}$	Propagation delay	See (5)		1.5	2.5	ns
$t_{JITTER-ADD}$	Additive Jitter	f_{IN} = 156.25 MHz, Input slew rate = 2 V/ns, Integration range = 12 kHz - 20 MHz		11	27	fs, RMS
R_{OUT}	Output impedance			52.5		Ω

VDD = 3.3 V ± 5 %, –40°C ≤ TA ≤ 125°C. Typical values are at VDD = 3.3 V, 25°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
CLOCK OUTPUT FOR V_{DD} = 1.8 V ± 5%						
V_{OH}	Output high voltage	I_{OH} = 1 mA	0.8 x V_{DD}			V
V_{OL}	Output low voltage	I_{OL} = 1 mA			0.2 x V_{DD}	V
$t_{RISE-FALL}$	Output rise and fall time	20/80%, C_L= 5 pF, f_{IN} = 156.25 MHz		0.38	1	ns
$t_{OUTPUT-SKEW}$	Output-output skew	See (4)			50	ps
$t_{PART-SKEW}$	Part-to-part skew				900	ps
$t_{PROP-DELAY}$	Propagation delay	See (5)		1.5	3	ns
$t_{JITTER-ADD}$	Additive Jitter	f_{IN} = 156.25 MHz, Input slew rate = 2 V/ns, Integration range = 12 kHz - 20 MHz		17.5	50	fs, RMS
R_{OUT}	Output impedance			60		Ω
GENERAL PURPOSE INPUT (1G)						
V_{IH}	High-level input voltage		0.75 x V_{DD}			V
V_{IL}	Low-level input voltage				0.25 x V_{DD}	V
I_{IH}	Input high-level current	V_{IH} = V_{DD_REF}	–50		50	µA
I_{IL}	Input low-level current	V_{IL} = GND	–50		50	µA

(1) Measured from VDD stable to output active, when 1G = HIGH.
(2) Measured from 1G rising edge crossing VIH to first rising edge of Yn.
(3) Measured from 1G falling edge crossing VIL to last falling edge of Yn.
(4) Measured from rising edge of any Yn output to any other Ym output.
(5) Measured from rising edge of CLKIN to any Yn output.

7.6 Timing Requirements

VDD = 3.3 V ± 5 %, –40°C ≤ TA ≤ 125°C

			MIN	NOM	MAX	UNIT
POWER SUPPLY						
V/t_{RAMP}	V_{DD} ramp rate		0.1		50	V/ms

7.7 Typical Characteristics

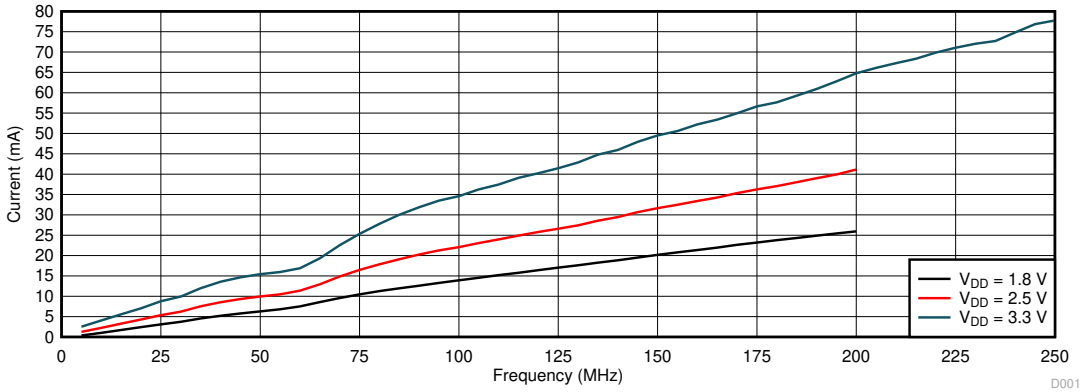


図 7-1. Device Power Consumption vs. Clock Frequency (Load 5 pF)

8 Parameter Measurement Information

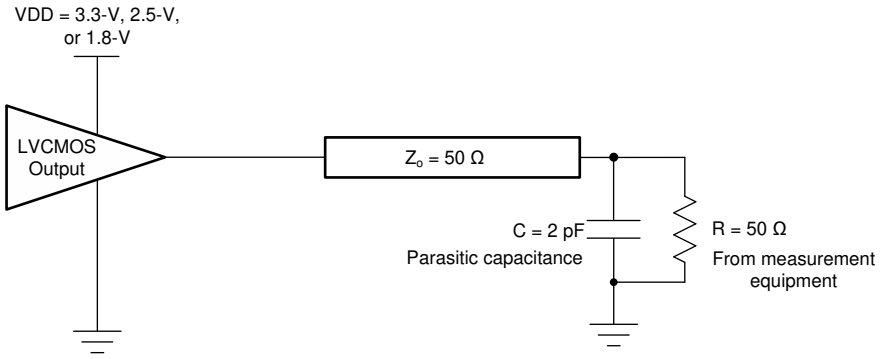


図 8-1. Test Load Circuit

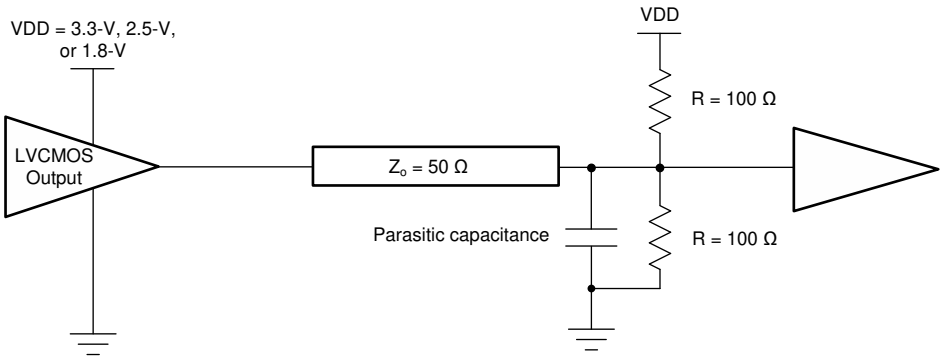


図 8-2. Application Load With 50-Ω Termination

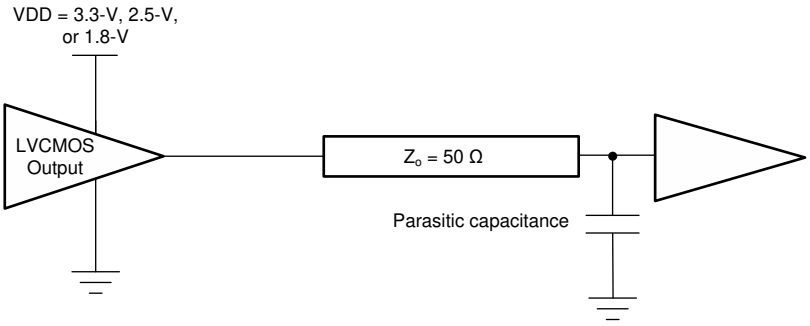


図 8-3. Application Load With Termination

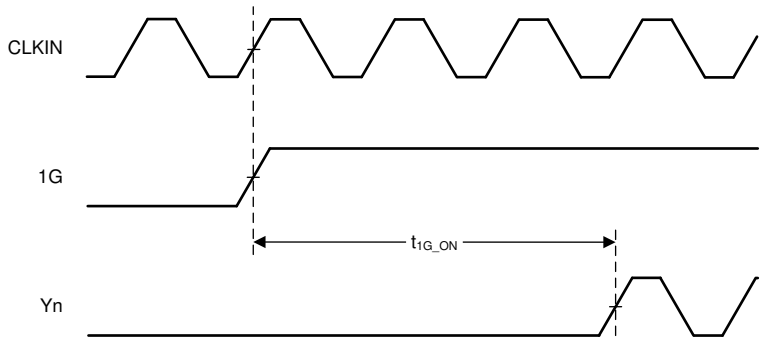


図 8-4. t_{1G_ON} Output Enable Time

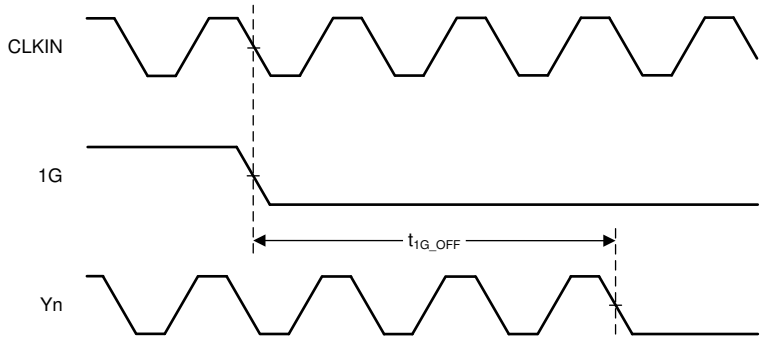


図 8-5. t_{1G_OFF} Output Disable Time

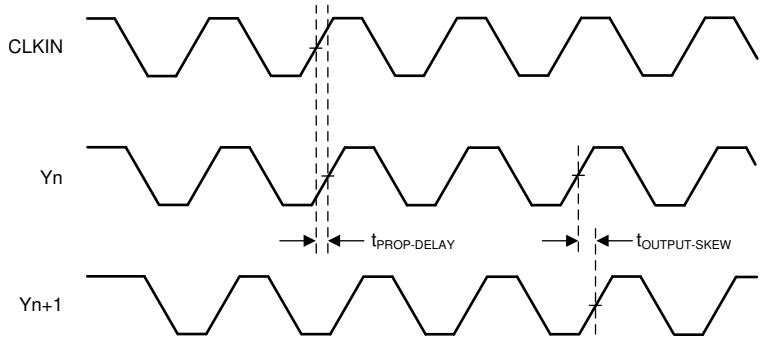


図 8-6. Propagation Delay $t_{PROP-DELAY}$ and Output Skew $t_{OUTPUT-SKEW}$

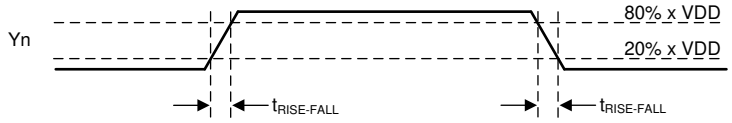


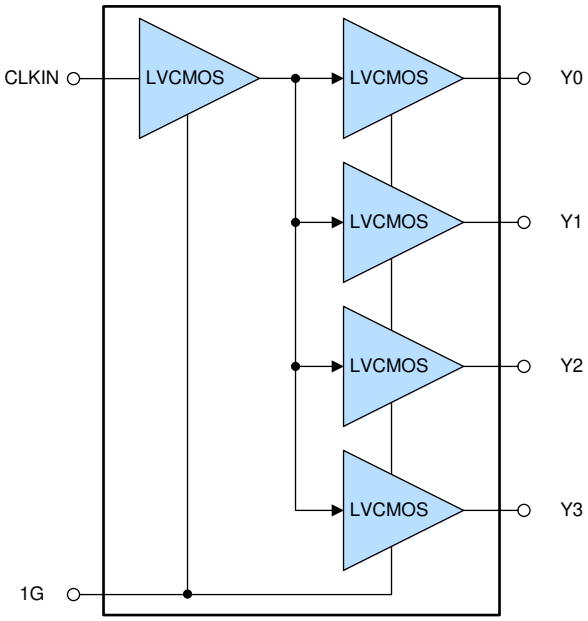
図 8-7. Rise and Fall Time $t_{RISE-FALL}$

9 Detailed Description

9.1 Overview

The LMK1C110x family of devices is part of a low-jitter and low-skew LVCMOS fan-out buffer solution. For best signal integrity, it is important to match the characteristic impedance of the LMK1C110x's output driver with that of the transmission line.

9.2 Functional Block Diagram



9.3 Feature Description

The outputs of the LMK1C110x can be disabled by driving the synchronous output enable pin (1G) low. Unused output can be left floating to reduce overall system component cost. Supply and ground pins must be connected to V_{DD} and GND, respectively.

9.3.1 Fail-Safe Inputs

The LMK1C110x family of devices is designed to support fail-safe input operation. This feature allows the user to drive the device inputs before VDD is applied without damaging the device. Refer to *Absolute Maximum Ratings* for more information on the maximum input supported by the device. The device also incorporates an input hysteresis that prevents random oscillation in absence of an input signal, allowing the input pins to be left open.

9.4 Device Functional Modes

The LMK1C110x operates from 1.8-V, 2.5-V, or 3.3-V supplies. 表 9-1 shows the output logics of the LMK1C110x.

表 9-1. Output Logic Table

INPUTS		OUTPUTS
CLKIN	1G	Yn
X	L	L
L	H	L
H	H	H

10 Application and Implementation

Note

以下のアプリケーション情報は、TI の製品仕様に含まれるものではなく、TI ではその正確性または完全性を保証いたしません。個々の目的に対する製品の適合性については、お客様の責任で判断していただくことになります。お客様は自身の設計実装を検証しテストすることで、システムの機能を確認する必要があります。

10.1 Application Information

The LMK1C110x family is a low additive jitter LVCMOS buffer solution that can operate up to 250-MHz at V_{DD} = 3.3 V and 200 MHz at V_{DD} = 2.5 V to 1.8 V. Low output skew as well as the ability for synchronous output enable is featured to simultaneously enable or disable buffered clock outputs as necessary in the application.

10.2 Typical Application

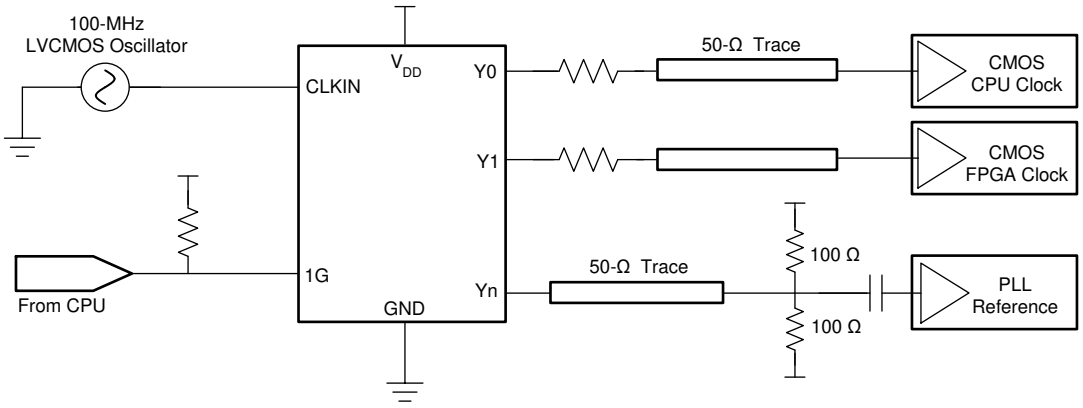


図 10-1. System Configuration Example

10.2.1 Design Requirements

The LMK1C110x shown in 図 10-1 is configured to fan out a 100-MHz signal from a local LVCMOS oscillator. The CPU is configured to control the output state through 1G.

The configuration example is driving three LVCMOS receivers in a backplane application with the following properties:

- The CPU clock can accept a full swing DC-coupled LVCMOS signal. A series resistor is placed near the LMK1C110x to closely match the characteristic impedance of the trace to minimize reflections.
- The FPGA clock is similarly DC-coupled with an appropriate series resistor placed near the LMK1C110x.
- The PLL in this example can accept a lower amplitude signal, so a Thevenin's equivalent termination is used. The PLL receiver features internal biasing, so AC coupling can be used when common-mode voltage is mismatched.

10.2.2 Detailed Design Procedure

Unused outputs can be left floating. See the *Power Supply Recommendations* section for recommended filtering techniques.

10.2.3 Application Curves

The low additive jitter of the LMK1C110x is shown in 図 10-2.

図 10-3 shows the low-noise 156.25-MHz reference source with 25.6-fs RMS jitter driving the LMK1C110x, resulting in 26.7-fs RMS jitter when integrated from 12 kHz to 20 MHz at 3.3-V supply. The resultant additive jitter measured is a low 7.6-fs RMS for this configuration.

図 10-4 shows the low-noise 156.25-MHz reference source with 25.6-fs RMS jitter driving the LMK1C110x, resulting in 27.5-fs RMS jitter when integrated from 12 kHz to 20 MHz at 2.5-V supply. The resultant additive jitter measured is a low 10-fs RMS for this configuration.

図 10-5 shows the low-noise 156.25-MHz reference source with 25.6-fs RMS jitter driving the LMK1C110x, resulting in 32-fs RMS jitter when integrated from 12 kHz to 20 MHz at 1.8-V supply. The resultant additive jitter measured is a low 19.2-fs RMS for this configuration.

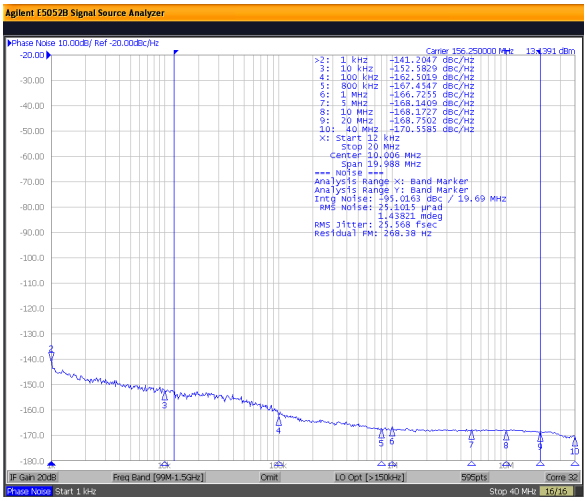


図 10-2. LMK1C110x Reference Phase Noise 25.6-fs (12 kHz to 20 MHz)

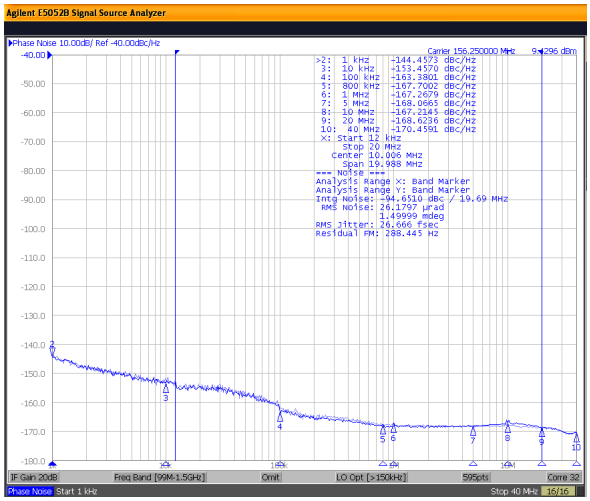


図 10-3. LMK1C110x 3.3-V Output Phase Noise 26.7-fs (12 kHz to 20 MHz)

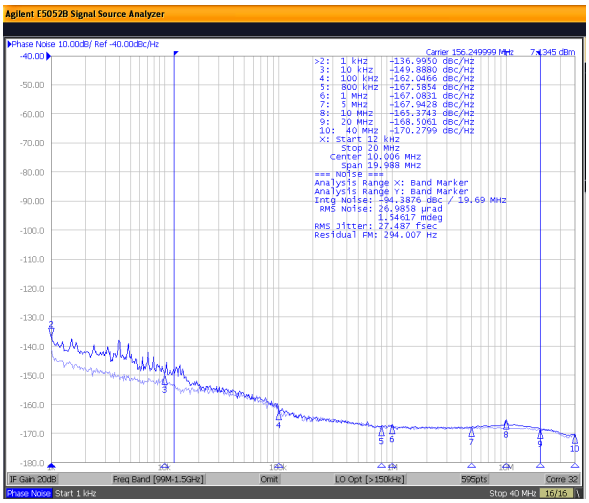


図 10-4. LMK1C110x 2.5-V Output Phase Noise 27.5-fs (12 kHz to 20 MHz)

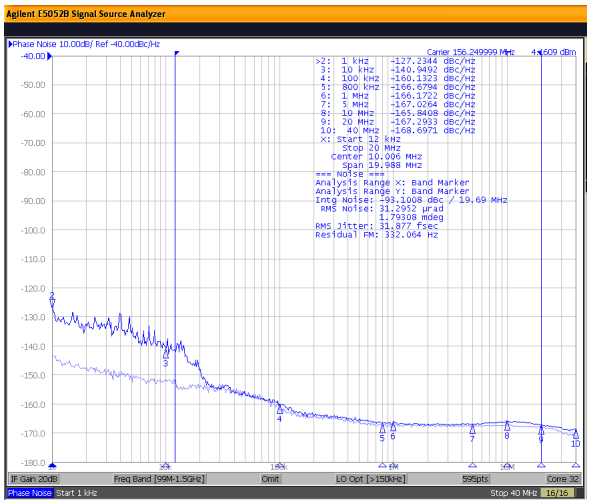


図 10-5. LMK1C110x 1.8-V Output Phase Noise 32-fs (12 kHz to 20 MHz)

11 Power Supply Recommendations

High-performance clock buffers can be sensitive to noise on the power supply, which may dramatically increase the additive jitter of the buffer. Thus, it is essential to manage any excessive noise from the system power supply, especially for applications where the jitter and phase noise performance is critical.

Filter capacitors are used to eliminate the low-frequency noise from the power supply, where the bypass capacitors provide the very low impedance path for high-frequency noise and guard the power supply system against induced fluctuations. These bypass capacitors also provide instantaneous current surges as required by the device and should have low equivalent series resistance (ESR). To properly bypass the supply, the decoupling capacitors must be placed very close to the power-supply terminals, be connected directly to the ground plane, and laid out with short loops to minimize inductance. TI recommends adding as many high-frequency (for example, 0.1 µF) bypass capacitors, as there are supply terminals in the package. TI recommends, but does not require, inserting a ferrite bead between the board power supply and the chip power supply that isolates the high-frequency switching noises generated by the clock buffer; these beads prevent the switching noise from leaking into the board supply. It is imperative to choose an appropriate ferrite bead with very low DC resistance to provide adequate isolation between the board supply and the chip supply, as well as to maintain a voltage at the supply terminals that is greater than the minimum voltage required for proper operation.

図 11-1 shows this recommended power supply decoupling method.

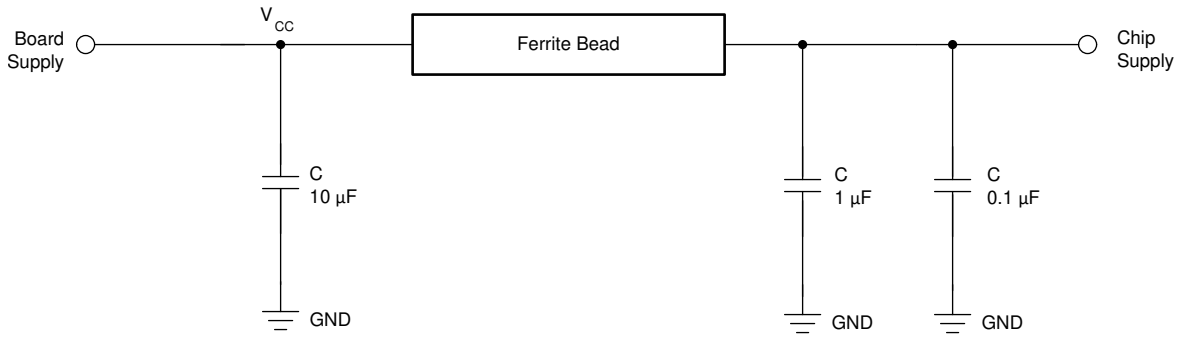


図 11-1. Power Supply Decoupling

12 Layout

12.1 Layout Guidelines

図 12-1 shows a conceptual layout detailing recommended placement of power supply bypass capacitors. For component side mounting, use 0402 body size capacitors to facilitate signal routing. Keep the connections between the bypass capacitors and the power supply on the device as short as possible. Ground the other side of the capacitor using a low-impedance connection to the ground plane.

図 12-2 provides a visual representation of the WSON device; it can be seen from the figure that similar to a DFN package, WSON doesn't have any leads.

12.2 Layout Example

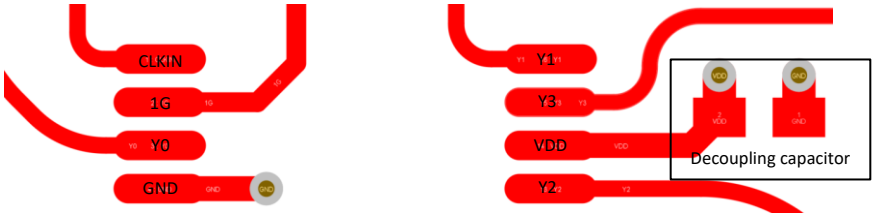


図 12-1. PCB Conceptual Layout

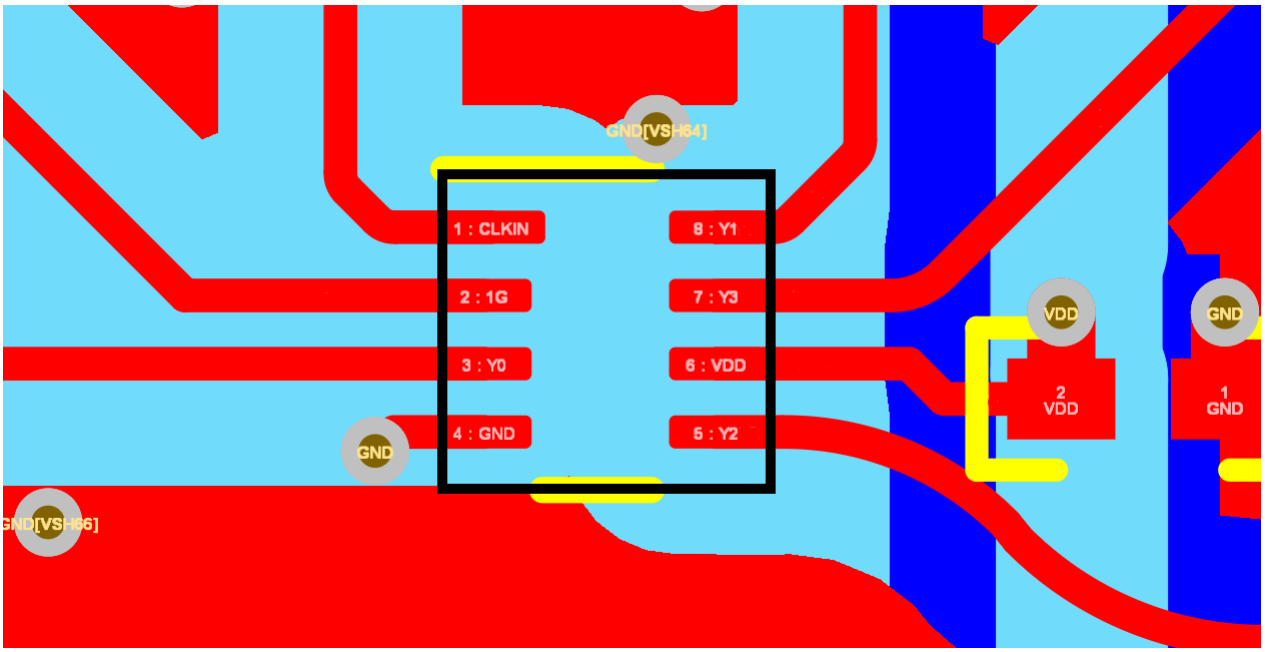


図 12-2. Layout illustration for 8-pin WSON device

13 Device and Documentation Support

13.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

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13.4 Electrostatic Discharge Caution

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

13.5 Glossary

TI Glossary — This glossary lists and explains terms, acronyms, and definitions.

14 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
LMK1C1102DQFR	ACTIVE	WSON	DQF	8	3000	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	L1C2	Samples
LMK1C1102DQFT	ACTIVE	WSON	DQF	8	250	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	L1C2	Samples
LMK1C1102PWR	ACTIVE	TSSOP	PW	8	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LMK1C2	Samples
LMK1C1103PWR	ACTIVE	TSSOP	PW	8	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LMK1C3	Samples
LMK1C1104DQFR	ACTIVE	WSON	DQF	8	3000	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	L1C4	Samples
LMK1C1104DQFT	ACTIVE	WSON	DQF	8	250	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	L1C4	Samples
LMK1C1104PWR	ACTIVE	TSSOP	PW	8	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LMK1C4	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

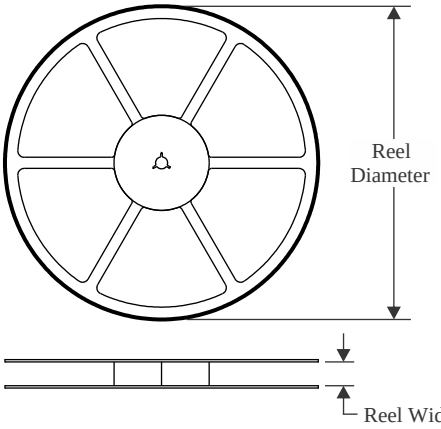
(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

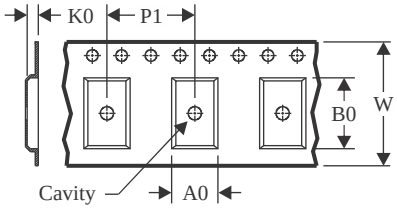
(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

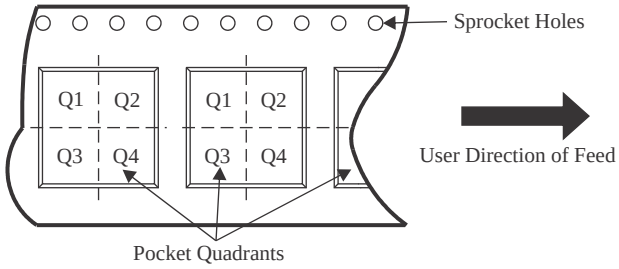


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

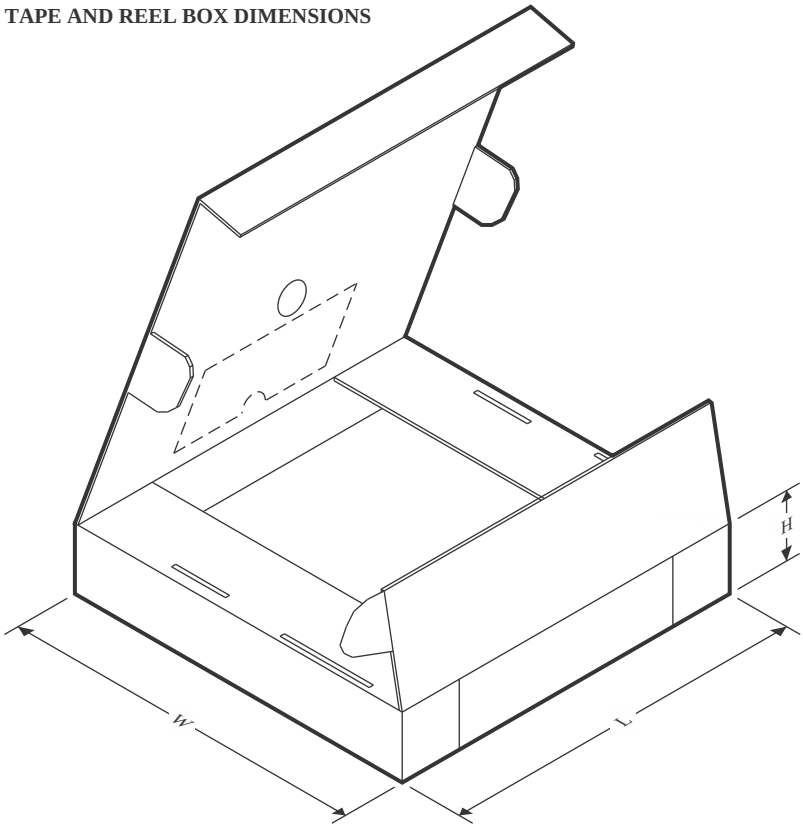
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LMK1C1102DQFR	WSON	DQF	8	3000	178.0	8.4	2.25	2.25	1.0	4.0	8.0	Q2
LMK1C1102DQFT	WSON	DQF	8	250	178.0	8.4	2.25	2.25	1.0	4.0	8.0	Q2
LMK1C1102PWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
LMK1C1103PWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
LMK1C1104DQFR	WSON	DQF	8	3000	178.0	8.4	2.25	2.25	1.0	4.0	8.0	Q2
LMK1C1104DQFT	WSON	DQF	8	250	178.0	8.4	2.25	2.25	1.0	4.0	8.0	Q2
LMK1C1104PWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS

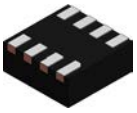


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LMK1C1102DQFR	WSON	DQF	8	3000	205.0	200.0	33.0
LMK1C1102DQFT	WSON	DQF	8	250	205.0	200.0	33.0
LMK1C1102PWR	TSSOP	PW	8	2000	356.0	356.0	35.0
LMK1C1103PWR	TSSOP	PW	8	2000	356.0	356.0	35.0
LMK1C1104DQFR	WSON	DQF	8	3000	205.0	200.0	33.0
LMK1C1104DQFT	WSON	DQF	8	250	205.0	200.0	33.0
LMK1C1104PWR	TSSOP	PW	8	2000	356.0	356.0	35.0

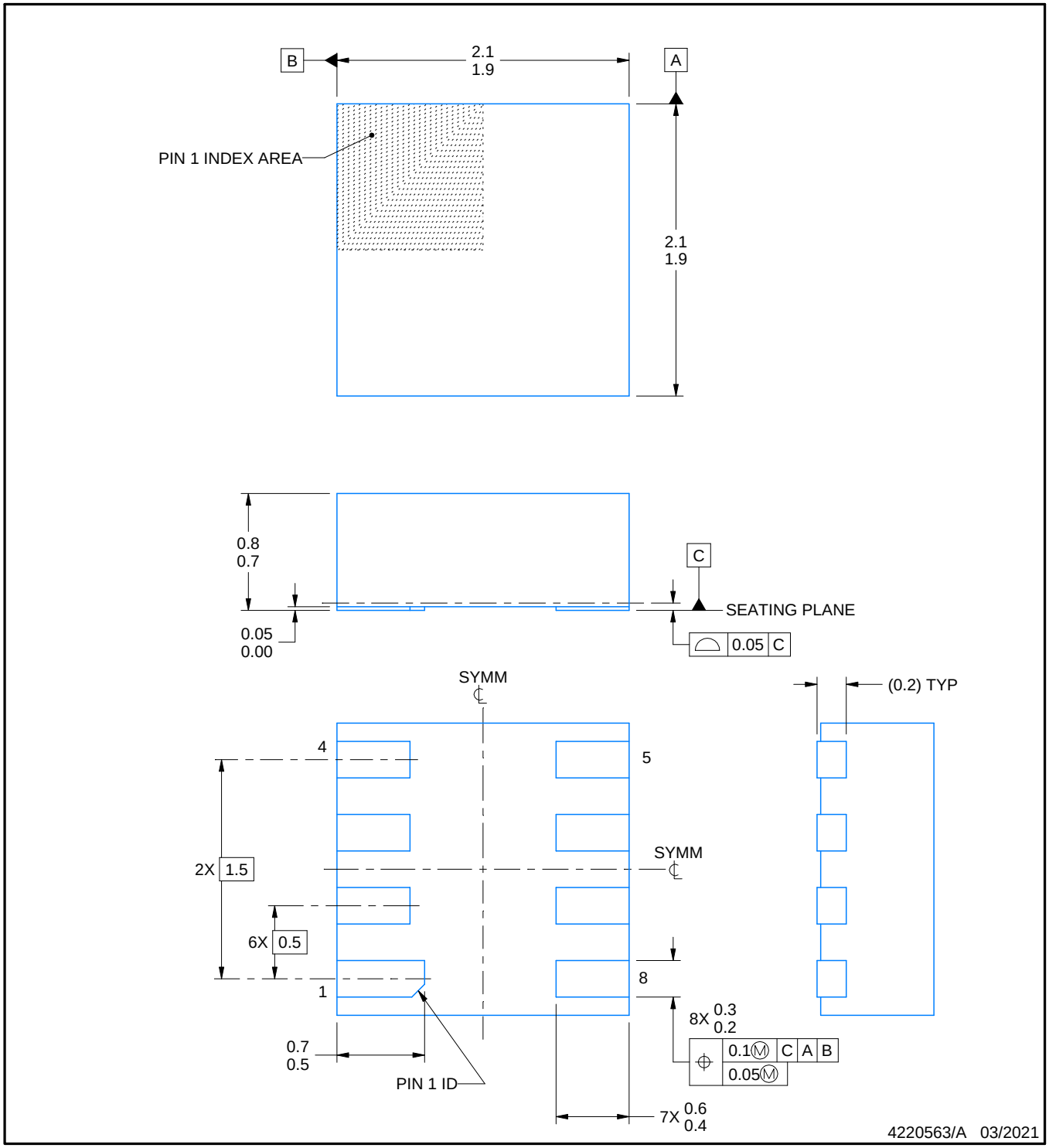
PACKAGE OUTLINE

DQF0008A



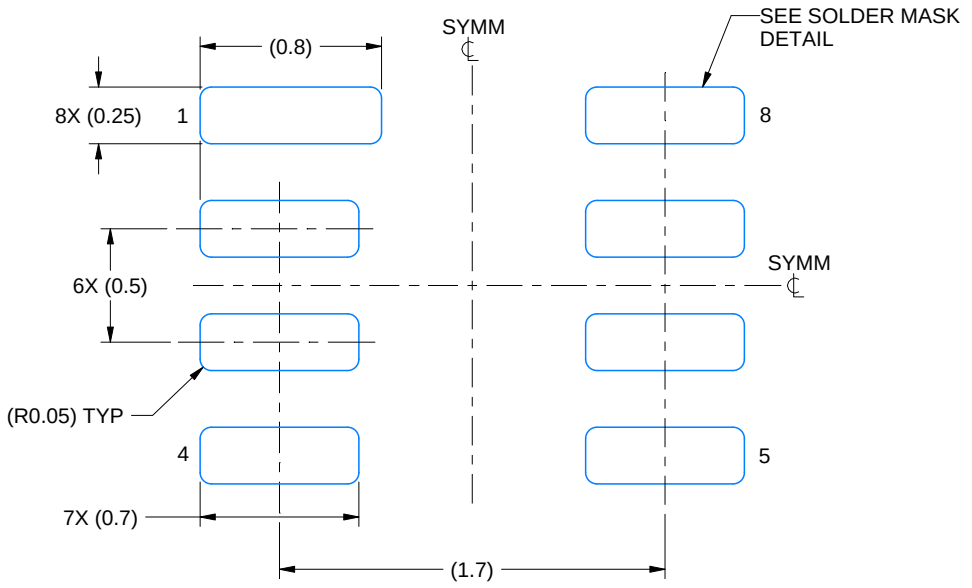
WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD

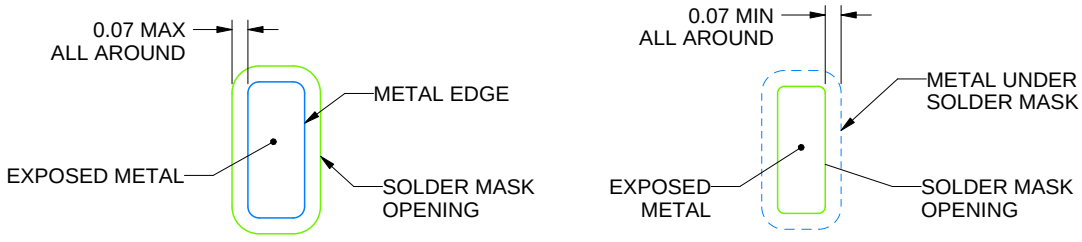


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 30X



SOLDER MASK DETAILS

4220563/A 03/2021

NOTES: (continued)

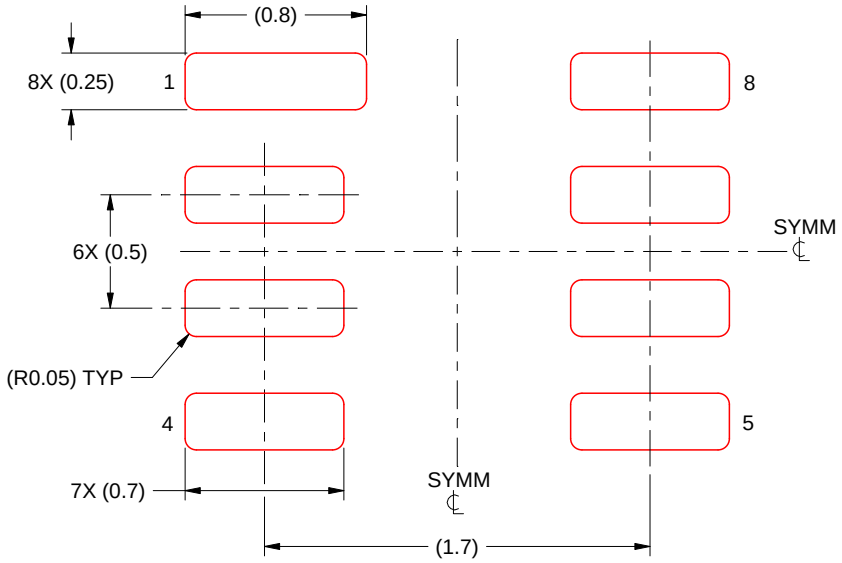
3. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).

EXAMPLE STENCIL DESIGN

DQF0008A

WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



SOLDER PASTE EXAMPLE
BASED ON 0.125 MM THICK STENCIL
SCALE: 30X

4220563/A 03/2021

NOTES: (continued)

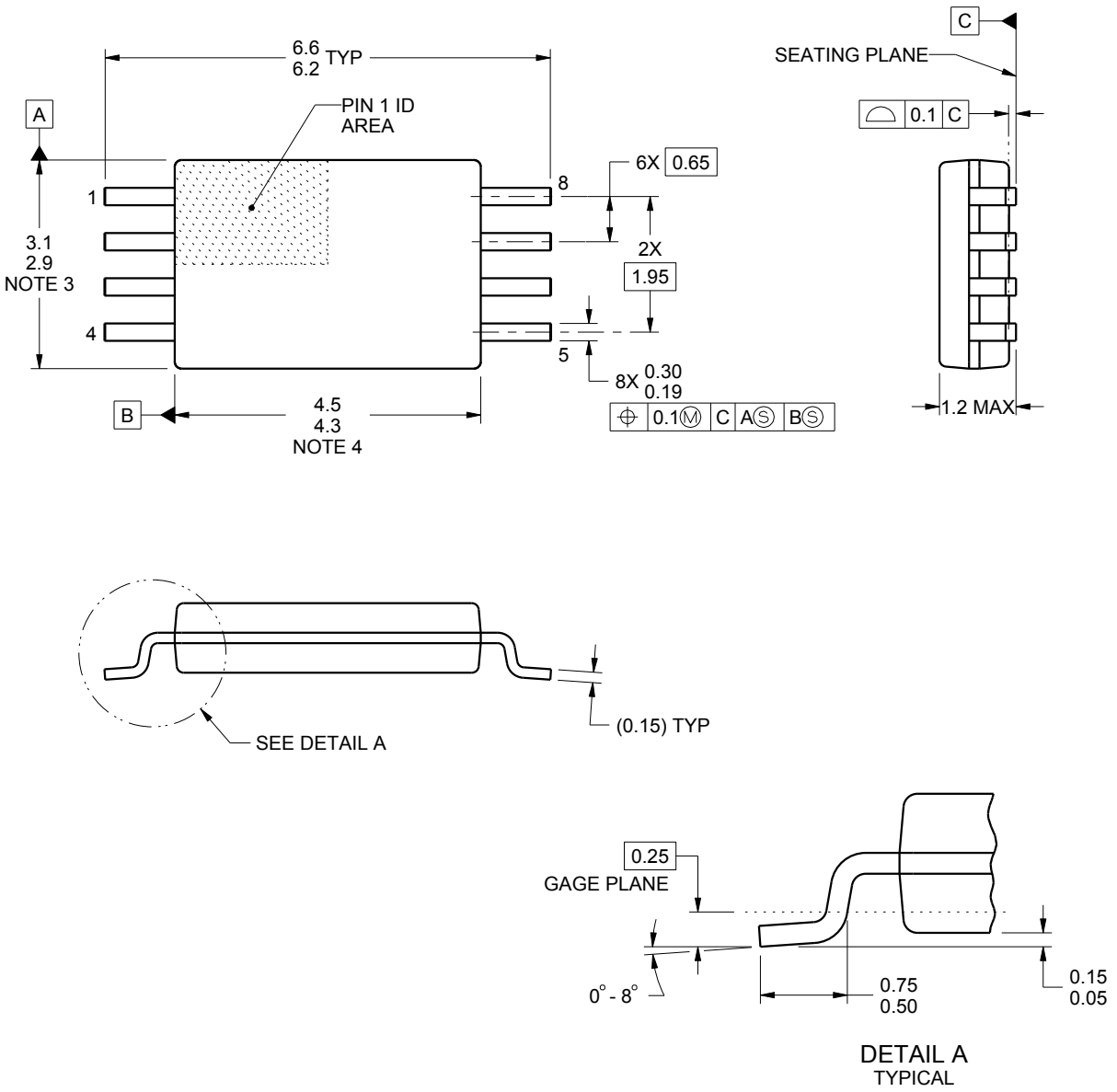
4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

PACKAGE OUTLINE

PW0008A

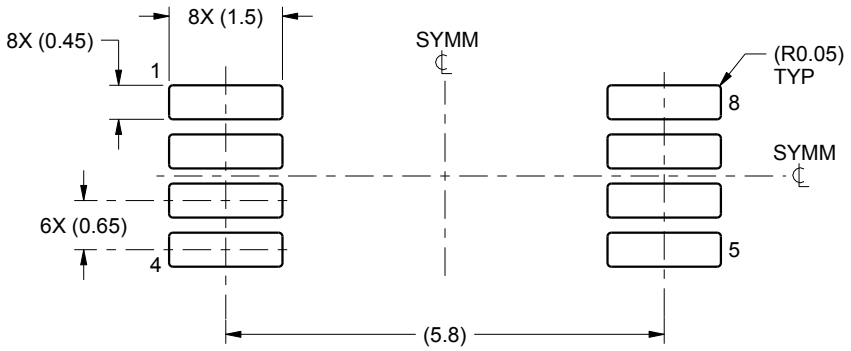
TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE

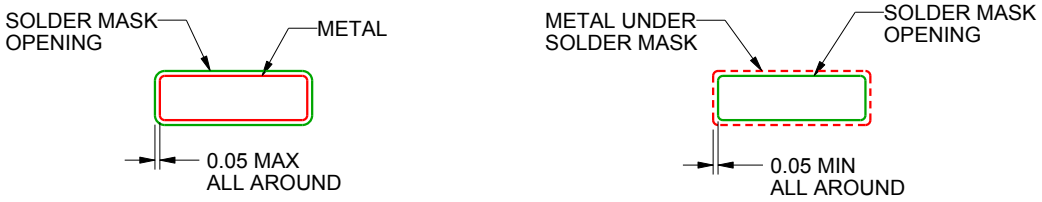


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153, variation AA.



LAND PATTERN EXAMPLE
SCALE:10X

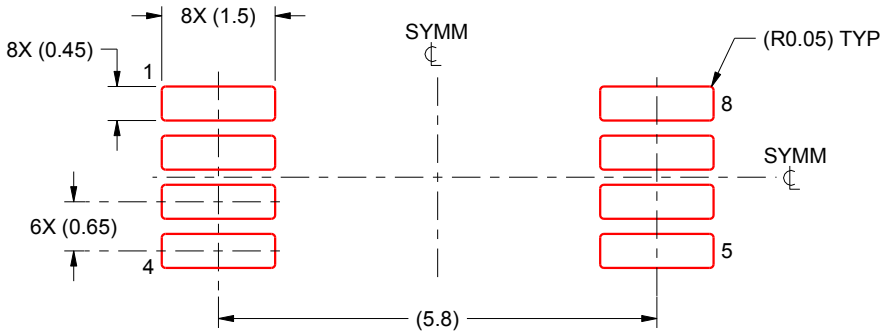


SOLDER MASK DETAILS
NOT TO SCALE

4221848/A 02/2015

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:10X

4221848/A 02/2015

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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